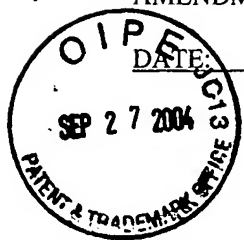


CERTIFICATE OF MAILING PURSUANT TO 37 C.F.R. §1.8

I hereby certify that this correspondence, pursuant to 37 C.F.R. §1.8, is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, MAIL STOP AMENDMENT, PO Box 1450, Alexandria, VA 22313-1450, on:



DATE: 9-24-2004

BY: Julie A. Eschke

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 C.F.R. §§1.97-1.98

PATENT APPLICATION

Applicant(s): Kaoru INOUE, et al.
Serial No.: 10/711,134
Group Art Unit: TBD
TITLE: SEMICONDUCTOR DEVICE

Docket No.: 28569.7636
Filing Date: August 26, 2004
Confirmation No.: 5133
Examiner: TBD

Commissioner for Patents
MAIL STOP AMENDMENT
PO Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. §1.56 and pursuant to 37 C.F.R. §§1.97-1.98, the reference or references listed and identified on the attached PTO-1449 based form are being submitted here for consideration by the Examiner. Any copy of the items listed on the enclosed copy of Form PTO-1449 that is not enclosed with this Information Disclosure Statement was previously cited by or submitted to the Patent and Trademark Office in the prior Parent Application, U.S. Serial No. 09/733,593, under 37 C.F.R. §1.98, which application was filed on December 8, 2000 and issued as U.S. Patent No. 6,639,255 on October 28, 2003.

The reference or references are being cited only in the interest of candor and without any admission that they constitute statutory prior art or contain matter which anticipates the invention or which would render the same obvious, either singly or in combination, to a person of ordinary skill in the art.



IFW

Serial No.: 10/711,134
Title: SEMICONDUCTOR DEVICE

This Information Disclosure Statement (IDS) is being filed under 37 C.F.R. §1.97(b)(1) as each item of information contained in this disclosure is being submitted within three months of the filing of this application, as such no fee should be required. If Applicant has overlooked any fees, however, the Commissioner is hereby authorized to debit Deposit Account No. 19-2814 for the same. **A duplicate copy of this Information Disclosure Statement is enclosed for this purpose.**

If there are any questions concerning this IDS, the Examiner is requested to contact the undersigned. If it is determined that this IDS has been filed under the wrong rule, the United States Patent and Trademark Office is requested to consider this IDS under the proper rule (with a petition if necessary) and charge the appropriate fee to Deposit Account No. 19-2814.

Respectfully submitted,

Date: 9-23-04

By S. Kelly for
Michael K. Kelly
Reg. No. 32,848
Reg. No. 45875

Enclosures: PTO-1449
Patent copies

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INFORMATION DISCLOSURE C1

(Use serial sheets if necessary)

ONP JC133351

SEP 27 2004

PATENT & TRADEMARK NUMBER

SERIAL NO. 10/711,134

FILING
August 26, 2004

GROUP	TBA
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[illegible][illegible]

			NG, "Complete Guide to Semiconductor Devices," 1995, McGraw-Hill, pp. 197-205
			Madelung, "Semiconductors--Basic Data, 2nd revised Edition," 1996, Springer, pp. 3-4 and 86-89.

DATE CONSIDERED

Form PTO-A820
(also form PTO-1449)

Patent and Trademark Office • U.S. DEPARTMENT OF COMMERCE

PAGE 1 OF 4

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



ATTY DOCKET NO.
28569.7636

SERIAL NO.
10/711,134

Karou INOUE, et al.

FILING
August 26, 2004

GROUP
TBA

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

			Dang, et al., "Fabrication and characterisation of enhanced barrier AlGaIn/GaNHFET," Electronic Letters, 1st April 1999, Vol. 35, No. 7, pp. 602-603
			Yu, et al., "Measurement of piezoelectrically induced charge in GaN/AlGaIn heterostructure field-effect transistors," Appl. Phys. Lett. 71 (19), 10 November 1997, pp. 2794-2796.

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

